

# STARPOWER

SEMICONDUCTOR

**FRED**

## FD300HFH60C1S

Molding Type Module

600V/300A 2 in one-package



### General Description

STARPOWER Diode Power Module provides low forward voltage as well as low reverse recovery loss. They are designed for the applications such as SMPS.

### Features

- Fast soft diode
- Low forward voltage drop
- Small temperature coefficient
- Low reverse recovery losses
- High ruggedness
- Low inductance
- Isolated copper baseplate using DBC technology

### Typical Applications

- SMPS
- PFC
- Electric welders
- DC choppers

**Absolute Maximum Ratings**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Description	FD300HFH60C1S	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	600	V
$I_F$	Continuous Forward Current	300	A
$I_{FRM}$	Repetitive Peak Forward Current	600	A
$P_D$	Maximum Power Dissipation @ $T_j=150^\circ\text{C}$	598	W
$T_{jmax}$	Maximum Junction Temperature	150	$^\circ\text{C}$
$T_{jop}$	Operating Junction Temperature	-40 to +125	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
$V_{ISO}$	Isolation Voltage RMS, $f=50\text{Hz}$ , $t=1\text{min}$	4000	V
M	Terminal Connection Torque, Screw M5 Mounting Torque, Screw M6	2.5 to 5.0 3.0 to 5.0	N.m
G	Weight of Module	150	g

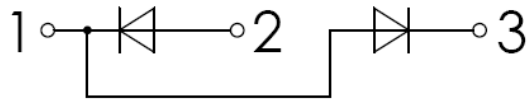
**Electrical Characteristics of Diode**  $T_C=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_F$	Diode Forward Voltage	$I_F=300\text{A}$	$T_j=25^\circ\text{C}$	1.40	1.80	V
			$T_j=125^\circ\text{C}$	1.45		
$I_R$	Diode Reverse Current	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$		1.0	mA
$Q_r$	Recovered Charge	$I_F=300\text{A}$ $V_R=300\text{V}$ $di/dt=-5500\text{A}/\mu\text{s}$	$T_j=25^\circ\text{C}$	16.4		$\mu\text{C}$
			$T_j=125^\circ\text{C}$	22.0		
$I_{RM}$	Peak Reverse Recovery Current	$I_F=300\text{A}$ $V_R=300\text{V}$ $di/dt=-5500\text{A}/\mu\text{s}$	$T_j=25^\circ\text{C}$	205		A
			$T_j=125^\circ\text{C}$	265		
$E_{rec}$	Reverse Recovery Energy	$I_F=300\text{A}$ $V_R=300\text{V}$ $di/dt=-5500\text{A}/\mu\text{s}$	$T_j=25^\circ\text{C}$	2.66		mJ
			$T_j=125^\circ\text{C}$	5.12		
$L_{CE}$	Stray Inductance				30	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal To Chip	$T_C=25^\circ\text{C}$		0.75		$\text{m}\Omega$

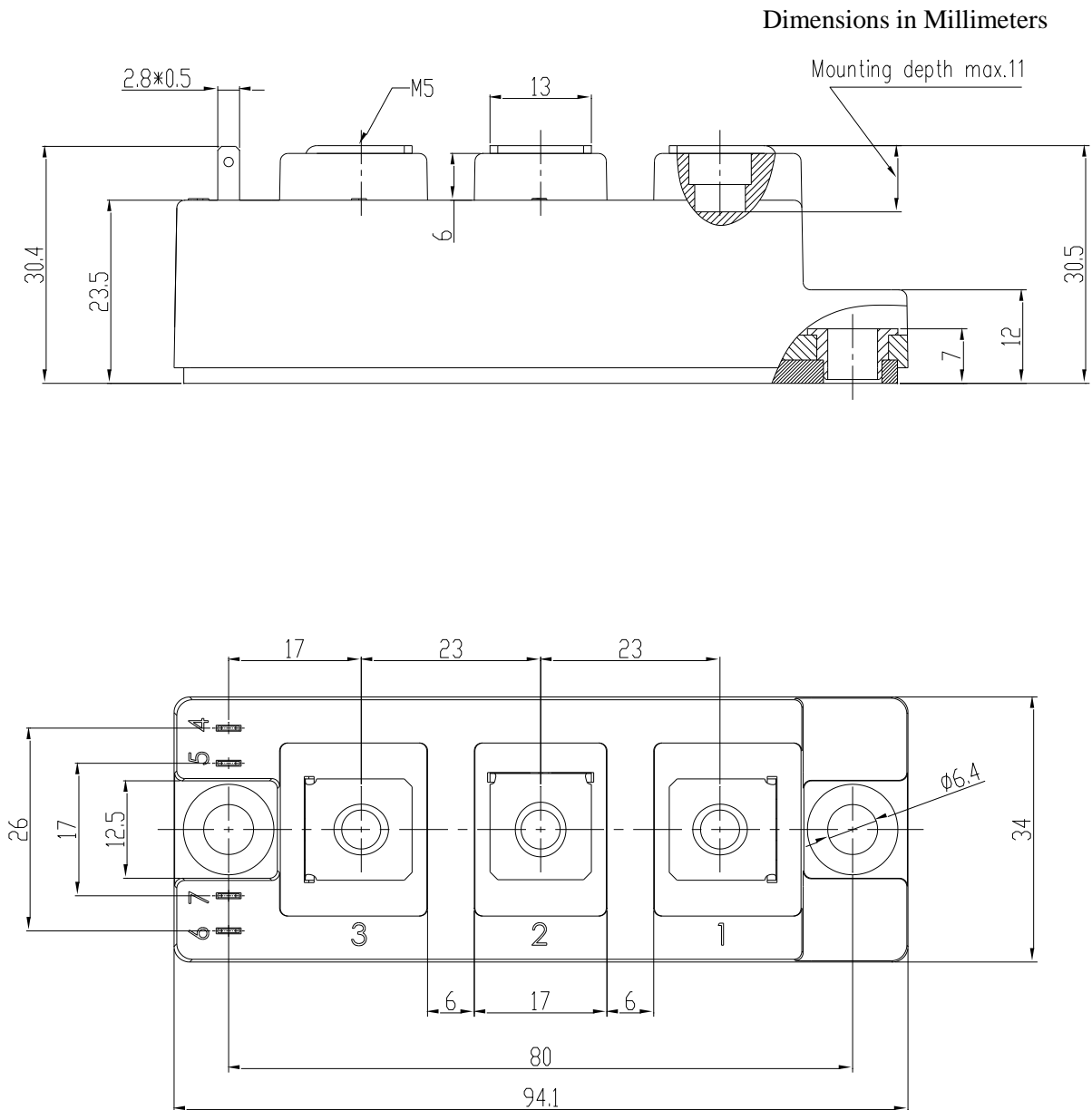
**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Junction-to-Case (per Diode)		0.209	K/W
$R_{\theta CS}$	Case-to-Sink (Conductive grease applied)	0.05		K/W

**Equivalent Circuit Schematic**



**Package Dimensions**



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